

L Number	Hits	Search Text	DB	Time stamp
49	1	("6730569").PN.	USPAT	2004/07/11 18:44
50	5	((("5841163") or ("5242849") or ("5786265")) or ("5432107") or ("4945066")).PN.	USPAT	2004/07/11 18:43
51	10	5242849.URPN.	USPAT	2004/07/11 18:26
52	299	(channel near3 stop) near3 (implant\$5 near2 region)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/11 18:57
53	106547	locos or fox or (field near2 oxide) or (local adj oxidation adj of adj silicon)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/11 18:32
54	242	((channel near3 stop) near3 (implant\$5 near2 region)) and (locos or fox or (field near2 oxide) or (local adj oxidation adj of adj silicon))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/11 18:32
55	155	((channel near3 stop) near3 (implant\$5 near2 region)) same (locos or fox or (field near2 oxide) or (local adj oxidation adj of adj silicon))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/11 18:32
57	166884	fet or (field near2 effect) near transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/11 18:33
58	4	((channel near3 stop) near3 (implant\$5 near2 region)) near (locos or fox or (field near2 oxide) or (local adj oxidation adj of adj silicon)) and (fet or (field near2 effect) near transistor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/11 18:33
56	33	((channel near3 stop) near3 (implant\$5 near2 region)) near (locos or fox or (field near2 oxide) or (local adj oxidation adj of adj silicon))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/11 18:36
59	376487	mos or (metal near2 oxide) near2 transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/11 18:37
60	26	(mos or (metal near2 oxide) near2 transistor) and ((channel near3 stop) near3 (implant\$5 near2 region)) near (locos or fox or (field near2 oxide) or (local adj oxidation adj of adj silicon))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/11 18:40
61	83	((channel near3 stop) near3 (implant\$5 near2 region)) same (locos or fox or (field near2 oxide) or (local adj oxidation adj of adj silicon)) and (mos or (metal near2 oxide) near2 transistor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/11 18:40
62	1275	((257/349) or (257/376) or (257/648) or (257/652) or (257/398) or (257/399) or (257/400)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/11 18:57
63	4	((257/349) or (257/376) or (257/648) or (257/652) or (257/398) or (257/399) or (257/400)).CCLS.) and (((channel near3 stop) near3 (implant\$5 near2 region)) same (locos or fox or (field near2 oxide) or (local adj oxidation adj of adj silicon))) and (mos or (metal near2 oxide) near2 transistor))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/11 18:57
64	11	4974051.URPN.	USPAT	2004/07/11 18:58
65	3	("4053916" "4591890" "4753896").PN.	USPAT	2004/07/11 18:59